

Supplementary Information for:

Engineering high charge transfer n-doping of graphene electrodes and its application to organic electronics

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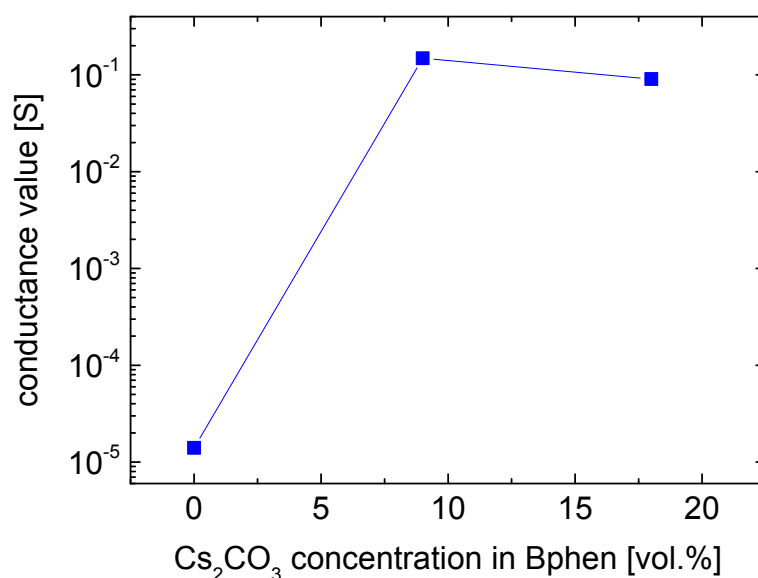


Figure S1: Conductance value of a 100nm Cs₂CO₃ doped Bphen layer with varying doping concentration.

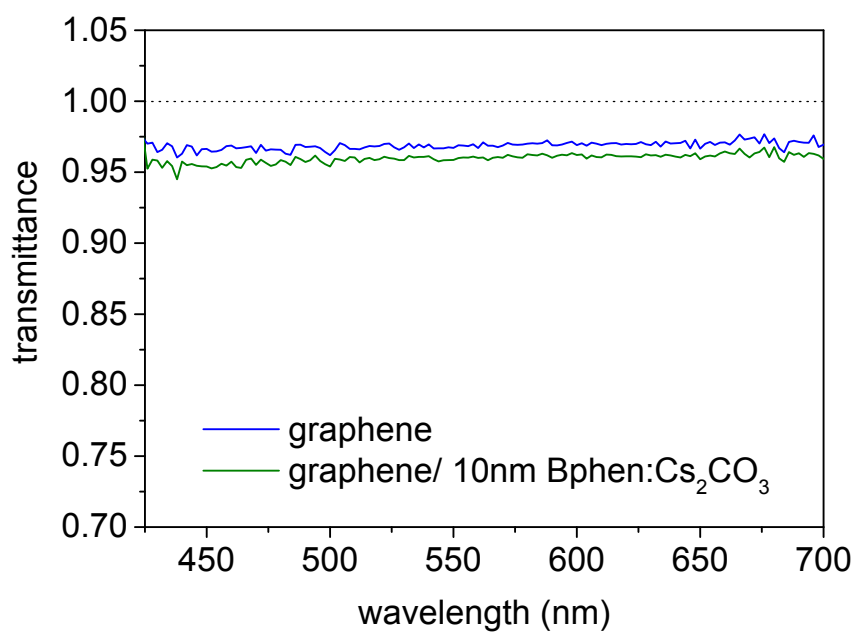


Figure S2: Transmittance characteristics of monolayer graphene and monolayer graphene with a 10nm Cs₂CO₃ doped Bphen layer (10 Vol.%) on top.